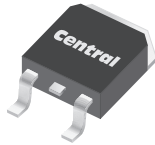


CSD-4M
CSD-4N

**SURFACE MOUNT
SILICON CONTROLLED RECTIFIERS
4.0 AMP, 600 THRU 800 VOLT**



DPAK CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CSD-4M and CSD-4N are epoxy molded SCRs designed for sensing circuit and control system applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CSD-4M	CSD-4N	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	600	800	V
RMS On-State Current ($T_C=85^\circ\text{C}$)	$I_T(\text{RMS})$	4.0		A
Peak One Cycle Surge Current, $t=10\text{ms}$	I_{TSM}	30		A
I^2t Value for Fusing, $t=10\text{ms}$	I^2t	4.5		A^2s
Peak Gate Power, $t_p=20\mu\text{s}$	P_{GM}	3.0		W
Average Gate Power Dissipation	$P_{G(AV)}$	0.2		W
Peak Gate Current, $t_p=20\mu\text{s}$	I_{GM}	1.2		A
Critical Rate of Rise of On-State Current	di/dt	50		$\text{A}/\mu\text{s}$
Operating Junction Temperature	T_J	-40 to +125		$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +150		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

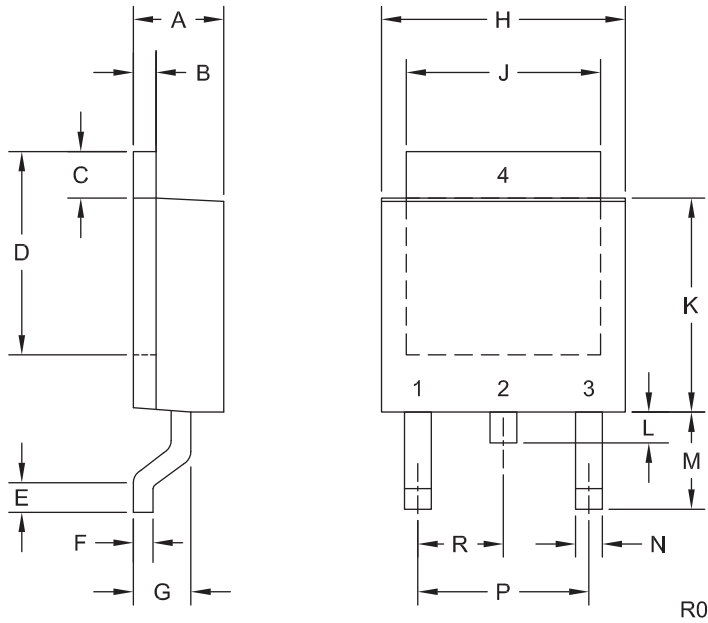
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, R_{GK}=1\text{K}\Omega$			10	μA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, R_{GK}=1\text{K}\Omega, T_C=125^\circ\text{C}$			200	μA
I_{GT}	$V_D=12\text{V}, R_L=10\Omega$	20	38	200	μA
I_H	$I_T=50\text{mA}, R_{GK}=1\text{K}\Omega$		0.25	2.0	mA
V_{GT}	$V_D=12\text{V}, R_L=10\Omega$		0.55	0.8	V
V_{TM}	$I_{TM}=8.0\text{A}, t_p=380\mu\text{s}$		1.6	1.8	V
dv/dt	$V_D=2/3 V_{DRM}, R_{GK}=1\text{K}\Omega, T_C=125^\circ\text{C}$	10			$\text{V}/\mu\text{s}$

CSD-4M
CSD-4N



**SURFACE MOUNT
SILICON CONTROLLED RECTIFIERS
4.0 AMP, 600 THRU 800 VOLT**

DPAK CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode
- 3) Gate
- 4) Anode

MARKING:

FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.083	0.108	2.10	2.75
B	0.016	0.032	0.40	0.81
C	0.035	0.063	0.89	1.60
D	0.203	0.228	5.15	5.79
E	0.020	-	0.51	-
F	0.018	0.024	0.45	0.60
G	0.051	0.071	1.30	1.80
H	0.248	0.268	6.30	6.81
J	0.197	0.217	5.00	5.50
K	0.209	0.245	5.30	6.22
L	0.025	0.040	0.64	1.02
M	0.090	0.115	2.30	2.91
N	0.012	0.045	0.30	1.14
P	0.180		4.60	
R	0.090		2.30	

DPAK (REV: R0)

R2 (21-January 2013)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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